

Description

The present invention relates to a slice amplifier

A slice amplifier plays an important role as an element of a very high speed data transmission system. For example, the slice amplifier is mounted in a data discrimination unit at a transmitter side or a receiver side of a pulse code modulation (PCM) optical communication system. The data discrimination unit contains, for example, a D-flip flop (FF) which produces logic "1" and "0" composing a base band data. At the D-FF, an input signal given to the D input terminal thereof, is sampled by a clock signal given to the C-input terminal thereof. In this case, if a phase deviation occurs in the input signal, it is difficult to correctly sample the input signal with a predetermined timing, and therefore, a data error will occur. Accordingly, the input signal is first sliced at a certain constant level, and then the peak-to-peak level is enlarged to obtain a rectangular-shaped waveform. In this case, the input signal can be discriminated to obtain correct data, even though a phase deviation has more or less occurred in the input signal. This is the function of the slice amplifier, which can be employed in a wave reshaping circuit.

From Technical Digest - Western Electric, No. 12, October 1968, pages 27-28 a clipping amplifier is known which clips the bottom portions of incoming pulses in order that sharp, well-defined signals be made available for application, for instance to a video circuit. This is performed with the aid of a diode which is reverse biased such that the magnitude of the reverse bias voltage is determined by the amplitude and time duration of the input pulses, i.e. by an integrating circuit. With this configuration only those parts of the input pulse appear at the output of the clipping amplifier which exceed the reverse bias voltage across the diode in magnitude. However, this circuit is not suitable for very high operating frequencies due to the use of conventional bipolar transistors which will not be able to perform the integration of the input signal properly, if an upper input frequency limit in the order of 100 MHz is exceeded. Further, the blocking capacitance of the diode with reverse bias will allow high frequency components below the clipping threshold to pass to the output of the clipping circuit, so that this circuit is not suitable for very high frequency operation.

Figure 1 is a schematic diagram of a conventional data discrimination unit including a slice amplifier. In Fig. 1, an input signal S_{in} is first received by a slice amplifier 11. The slice amplifier 11 constitutes, together with a wave reshaping part 12 following the amplifier 11, a data discrimination unit 10. The input signal S_{in} is an analog signal having the waveforms as shown, and each waveform represents a data logic "0" or "1". Although the waveforms have already passed through an equalizer (not shown), each waveform

still has a peak shape. Whether each mountain-shaped waveform represents a data logic "0" or "1" is determined by a waveform reshaping part 12, which is comprised of a D-flip flop (FF) for sampling each waveform by using a constant clock CLK. In this case, of course, the inherent digital output data D_{out} can be reproduced if the waveform is correctly sampled by the clock CLK. If, however, the phase deviation occurs in the clock CLK, the clock timing cannot be aligned with the top of each peak of the waveform, and therefore the clock samples the valley portion between the two adjacent peak waveforms, and thus a discrimination error is produced.

To overcome the problem of phase deviation, the waveform of the input signal S_{in} is sliced at a certain level, for example, a level TH, and the thus-sliced signal is then transformed into a rectangular-shaped waveform signal which is an output signal S_{out} .

Therefore, the data logic "1" can be correctly sampled even if there is a more or less phase deviation of the clock. Namely, the slice amplifier 11 achieves the aforesaid transformation of the signal, i.e., $S_{in} \rightarrow S_{out}$.

Figure 2 is a circuit diagram illustrating an example of a prior art slice amplifier. The prior art slice amplifier 11 is comprised of a first bipolar transistor Q_1 receiving the input signal S_{in} at its base, a second bipolar transistor Q_2 receiving a reference voltage V_{ref} at its base, and producing the output signal S_{out} , and a constant current source CS, and thus forms, as a whole, a current switch.

The prior art slice amplifier of the bipolar transistor type shown in Fig. 2 cannot cope with very high speed data transmission because, due to the operation limit of the bipolar transistor per se, the slice amplifier is limited to a data transmission maximum speed on the order of 500 Mb/s.

The present invention is based on the employment of a field effect transistor (FET), instead of the bipolar transistor, to abolish this operation limit. For example, a GaAs-FET or a high electron mobility transistor, so-called HEMT, can raise the operation limit up to the order of several G b/s. In view of this, the inventors have attempted to replace the bipolar transistors Q_1 and Q_2 in the slice amplifier with FET's.

Figure 3 is a circuit diagram of a prototype slice amplifier using FET's. The slice amplifier 21 contains the FET's T_1 and T_2 , instead of the bipolar transistors Q_1 and Q_2 contained in the slice amplifier 11. Note, the meanings of the characters S_{in} (input signal), S_{out} (output signal, i.e., sliced signal), CS (constant current source), and so on have been already explained.

The inventors, however, found that the slice amplifier 21 cannot be practically used. This is because, first, the variance of the pinch-off voltage (V_p) of each FET is too large, that is, the FET's have different pinch-off voltage (V_p) to each other, and second, the pinch-off voltage (V_p) per se is susceptible

to variations of temperature.

Figure 4 depicts characteristic curves in the $I_D - V_{GS}$ of an FET. This characteristic curve is typical for usual FET. When the input signal S_{in} is applied to the gate of the FET, the hatching portion thereof is cut away if the related FET has the characteristic curve I. Alternatively, if another FET having the characteristic curve II is used, the whole of the signal S_{in} will be in cut away. In general, the FET exhibits a characteristic curve, i.e., $I_D - V_{GS}$, which is analogous to that of a vacuum tube. In this case, the gate-source voltage V_{GS} at the drain current I_D of zero, i.e., the aforesaid pinch-off voltage, varies, in actuality, over a range as large as 1 V through 4 V in each FET. Due to this nonuniformity of the $I_D - V_{GS}$ characteristics, it is almost impossible to realize a current switch available for a slice amplifier. In the circumstances it may be possible to eliminate the nonuniformity of the $I_D - V_{GS}$ characteristics by fabricating FET's on the same semiconductor chip in the form of an integrated circuit (IC). But, the slice amplifier is not inherently expected to be mass produced, and therefore, a problem arises in that the cost of the slice amplifier will increase due to the employment of the IC process.

Further, as another disadvantage, the pinch-off voltage is also susceptible to variations of temperature.

Fig. 5 depicts characteristic curves in the $I_D - V_{GS}$ of an FET in relation to a temperature variation. In Fig. 5, curves III, IV and V represent $I_D - V_{GS}$ characteristics obtained at a low temperature, a median temperature (room temperature) and a high temperature. It is apparent that the curves are not uniform, and that the pinch-off voltage V_p varies accordingly. Thus, the output signal S_{out} with respect to the input signal S_{in} is not stable.

A similar variation of the pinch-off voltage V_p also occurs in response to a variation of a power source voltage.

In view of the above-mentioned problems, the object of the present invention is to provide a slice amplifier which can stably and correctly produce the output signal without being affected by, for example, variance of semiconductor component characteristics, variance of the temperature, and variance of the power source voltage.

This object is solved by the use of field effect transistors (FET's) operative to discriminate logics "0" and "1" of an input signal, and comprising : a first FET for receiving, at a gate thereof, an input signal and outputting, at a drain thereof, a portion of said input signal which is above a predetermined first slice level ; a first monitor and control unit for receiving, from said first FET, a drain output as a first sliced signal and detecting lower limit level of said first sliced signal to control a gate-source voltage of said first FET so that the thus-detected limit level is maintained at a predetermined first constant level ; a second FET for receiv-

ing, at a gate thereof, a drain output from said first FET and outputting, at a drain of said second FET, a portion of said first sliced signal which is above a predetermined second slice level and ; a second monitor and control unit for receiving, from said second FET, a drain output as a second sliced signal and detecting lower limit level of said second sliced signal to control a gate-source voltage of said second FET so that the thus-detected limit level is maintained at a predetermined second constant level, thus said second sliced signal is produced as an output signal with respect to said input signal.

Further embodiments of the present invention will become apparent from the subclaims.

Now the invention will be described with reference to the accompanying drawings.

Fig. 1 is a schematic diagram of a conventional data discrimination unit including a slice amplifier ;

Fig. 2 is a circuit diagram illustrating an example of a prior art slice amplifier ;

Fig. 3 is a circuit diagram of a prototype slice amplifier using FET's ;

Fig. 4 depicts characteristic curves in the $I_D - V_{GS}$ of an FET ;

Fig. 5 depicts characteristic curves in the $I_D - V_{GS}$ of an FET in relation to temperature variations ;

Fig. 6 is a circuit diagram illustrating a basic arrangement of a slice amplifier according to the present invention ;

Figs. 7A, 7B and 7C depict waveforms of signals appearing at the portions A, B and C indicated in the circuit of Fig. 6 ;

Fig. 8A and 8B depict characteristic curves for explaining the waveforms shown in Figs. 7A and 7C, respectively ;

Fig. 9 is a circuit diagram of a slice amplifier according to a first embodiment of the present invention ;

Fig. 10 is a circuit diagram illustrating an example of the lower limit level detector of Fig. 9 ;

Fig. 11 is a circuit diagram illustrating an example of the current sink means of Fig. 9 ;

Fig. 12 is a detailed circuit diagram illustrating an example of an actual slice amplifier together with its peripheral circuit elements ; and,

Fig. 13 is a circuit diagram of a slice amplifier according to a second embodiment of the present invention.

BEST MODE FOR CARRYING OUT THE INVENTION

Figure 6 is a circuit diagram illustrating a basic arrangement of a slice amplifier according to the present invention. In Fig. 6, a slice amplifier 31 is comprised of a first FET T_1 , a second FET T_2 , a first monitor and control unit 41, which monitors a first

slice signal S_{s1} from the FET T_1 and controls the gate-source voltage V_{GS} of the FET T_1 , and a second monitor and control unit 42, which monitors a second sliced signal S_{s2} from the FET T_2 and controls the gate-source voltage V_{GS} of the FET T_2 . The second sliced signal S_{s2} per se is used as the output signal S_{out} to be obtained. The first monitor and control unit 41 controls, as mentioned above, the gate-source voltage V_{GS} of the first FET T_1 . Therefore, the unit 41 is not limited to control of the source voltage of the FET₁, as shown by a solid line, but also can control the gate voltage thereof, as shown by a broken line. This also holds true for the second monitor and control unit 42 in relation to the second FET T_2 . This will be exemplified hereinafter.

The first FET T_1 receives the input signal S_{in} at its gate and slices the waveform of the received signal S_{in} , the peak of which is higher than a first slice level (SL_1), and thereby obtains the first sliced signal S_{s1} . The signal S_{s1} appears at the drain of the first FET T_1 , and the drain output voltage is always monitored by the first monitor and control unit 41, which controls the source voltage of the FET T_1 so that the lower limit level of the drain output voltage of T_1 is maintained at a predetermined first constant level (CL_1).

The second FET T_2 receives the first sliced signal S_{s1} at its gate, and slices the waveform of the signal S_{s1} , the peak of which is higher than a second slice level (SL_2), thereby obtaining a second sliced signal S_{s2} . The signal S_{s2} appears at the drain of the second FET T_2 , and the drain output voltage is always monitored by the second monitor and control unit 42 which controls the source voltage of the FET T_2 so that the lower limit level of the drain output voltage of T_2 is maintained at a predetermined second constant level (CL_2). Thus, the drain output voltage, i.e., the second sliced signal S_{s2} , is produced as the output signal S_{out} of the slice amplifier 31. The above-mentioned operation will be further clarified with reference to the related waveforms.

Figures 7A, 7B, and 7C depict waveforms of signals appearing at the portions A, B, and C indicated in the circuit of Fig. 6. Figures 8A and 8B depict characteristic curves for explaining the waveforms shown in Figs. 7A and 7C, respectively. The input signal S_{in} is sliced at the first slice level SL_1 , as shown in Figs. 7A and 8A. The slice level SL_1 is preferably determined as the pinch-off voltage V_p , as shown in Fig. 8A, and thus the first sliced signal S_{s1} is produced in accordance with the characteristic curve ($I_D - V_{GS}$) of Fig. 8A. The lower limit level of the first sliced signal S_{s1} is maintained at the first constant level CL_1 , as shown in Fig. 7B, by the first monitor and control unit 41. Note, the first slice level SL_1 can be commonly used for the discrimination of the data logic "0" or "1" contained in the input signal S_{in} .

The first sliced signal S_{s1} is then applied to the gate of the second FET T_2 and sliced at the second

slice level SL_2 to produce the second sliced signal S_{s2} , as shown in Fig. 8B. The lower limit level of the second sliced signal S_{s2} is maintained at the second constant level CL_2 , as shown in Fig. 7C, by the second monitor and control unit 42. The second slice level SL_2 is preferably determined to be a level which is suitable as an input level of a logic circuit (not shown) which follows after the slice amplifier 31.

In Figs. 7B and 7C, GND represents a ground level with respect to a power source level $-V_{ss}$, for example, -12 V. In Fig. 7B, the level CL_1 is, for example, -1.6 V. In Fig. 7C, the level CL_2 is, for example, -1.6 V, and the level V_2 is, for example, -0.8 V.

The above explanation has been made by taking a case where the lower limit level of the first sliced signal S_{s1} is maintained at the first constant level CL_1 , and the lower limit level of the second sliced signal S_{s2} is maintained at the second constant level CL_2 . Note, it is important to set the first and second sliced signals S_{s1} and S_{s2} , as a whole, at a respective fixed potential.

Figure 9 is a circuit diagram of a slice amplifier according to a first embodiment of the present invention. Members identical to those of previous figures are represented by the same reference numerals or characters. In the first embodiment, the first and second FET's T_1 and T_2 are provided, at their sources, with capacitors C_1 and C_2 , respectively. The capacitors C_1 and C_2 are included in the monitor and control units 41 and 42 for receiving the respective source voltages which are grounded thereby in terms of AC voltage, and thus a high frequency characteristic is not deteriorated. The monitor and control units 41 and 42 have substantially the same construction. The only difference between the two is that the former contains a reference voltage source of V_{ref} , and the latter contains a reference voltage source of V'_{ref} .

These reference voltages can be determined freely, but are later fixed once the respective suitable levels are determined. The reference voltages V_{ref} and V'_{ref} specify the lower limit levels of the first and second sliced signals S_{s1} and S_{s2} , respectively. As can be seen from the monitor and control unit 41, the unit 41 is comprised of a first detection means, i.e., a lower limit level detector 43, a first comparison means, i.e., an error amplifier 45, and a constant voltage generation means, i.e., a current sink means 47. The second monitor and control unit 42 has the same construction. That is, the unit 42 has a lower limit level detector 44, an error amplifier 46, and a current sink means 48. Taking the first monitor and control unit 41 as an example, when the lower limit level of the drain output voltage of the FET T_1 , i.e., the first sliced signal S_{s1} , goes lower (or higher) than the first reference voltage level (V_{ref}), the lower (or higher) error level is detected by the lower limit level detector 43 and the output from the detector 43 is amplified by the error amplifier 45 to apply the amplified error level to the

of input of the current sink means 47, which increases (or decrease) the source voltage of the FET₁ to increase (or decrease) the lower limit level of the signal S_{s1} , to thereby maintain the lower limit level at the first constant level CL_1 . The above-mentioned operation also holds true for the second monitor and control unit 42, so as to maintain the lower limit level of the second sliced signal S_{s2} at the second constant level CL_2 . As apparent from the above description, the first and second monitor and control units 41 and 42, respectively, control the source voltages of the FET's T_1 and T_2 , while keeping their gate voltages at a fixed level, so that each gate-source voltage V_{GS} of the FET's T_1 and T_2 is controlled.

In Fig. 9, a zener diode ZD is inserted between the drain of the first FET T_1 and the gate of the second FET T_2 , which zener diode ZD acts as a DC level shifter. The diode ZD decreases the input level to be applied to the second FET T_2 by, for example about 5 V, to assure an optimum driving level for the second FET T_2 .

Further, in Fig. 9, resistors 49 and 50 are connected to the gates of the first and second FET's T_1 and T_2 . The resistor 49 (and the resistor 50) is a so-called gate resistor which is useful for preventing undesired oscillation of the first FET T_1 (and the second FET T_2). It is known that the input impedance of the FET often assumes a negative resistance, which may induce oscillation. The negative resistance is changed to a positive resistance by the addition of the resistor (49, 50).

In Fig. 9, the second slice level (SL_2) is preferably determined to be a level suitable as an input level of a logic circuit, as mentioned previously. If the output signal S_{out} is given to an emitter coupled logic (ECL) circuit, a diode D_1 is employed for the determination of the upper level of the output signal S_{out} (V_2). The diode D_1 operates as a DC level shifter with, for example, -0.8 V. Thus, the diode D_1 defines an upper limit level, i.e., -0.8 V, of a prescribed range (-0.8 V through -1.6 V). The ECL circuit is a high speed logic circuit for forming the D-flip flop FF shown in Fig. 1.

The waveforms of signals appearing at the portions A, B, and C have already been displayed with reference to Figs. 7A, 7B, and 7C.

Figure 10 is a circuit diagram illustrating an example of the lower limit level detector of Fig. 9. In Fig. 10, the detector 43 (and the detector 44) is connected between the FET T_1 (T_2) and the error amplifier 45 (46). A diode D_2 is connected with the drain of the FET T_1 (T_2) and made conductive every time the cathode level becomes lower than the anode level, so that a capacitor C_3 is charged to hold each lower limit level of the signal S_{s1} (S_{s2}). The charging voltage is applied to the error amplifier 45 (46).

Figure 11 is a circuit diagram illustrating an example of the current sink means of Fig. 9. In Fig. 11, the current sink means 47 (and the generator 48)

is connected between the error amplifier 45 (46) and the FET T_1 (T_2). As apparent from Fig. 11, the constant voltage generator 47 (48) is formed as a so-called series regulator having a transistor Q_3 . The transistor Q_3 receives, at its base, the output from the error amplifier 45 (46) and maintains the source voltage of the FET T_1 (T_2) at a constant level.

Figure 12 is a detailed circuit diagram illustrating an example of an actual slice amplifier together with its peripheral circuit elements. In Fig. 12, members corresponding to those previously explained are indicated by the same reference numerals or characters. An equalizer 51 is mounted at a stage preceding the slice amplifier 31. The waveform reshaping part 12 (Fig. 1) is mounted at a following stage thereof. Reference numerals 52 and 53 represent usual ECL gates. The majority of the slice amplifier 31 of Fig. 12 is the same as previously explained, the only difference being that buffer amplifiers 43-3 and 44-3 are positively illustrated in this figure. It should be understood that the lower limit level detector 43 (and the detector 44) are classified into three parts, 43-1, 43-2, and 43-3 (and the parts 44-1, 44-2, and 44-3).

Figure 13 is a circuit diagram of a slice amplifier according to a second embodiment of the present invention. The difference between the aforesaid first embodiment and the second embodiment is that, in the second embodiment, the gate-source voltage V_{GS} of the FET is varied by controlling the gate voltage, not the source voltage as in the first embodiment. It should be understood that only an input side stage of the slice amplifier is illustrated for brevity. A monitor and control unit (corresponding to the first monitor and control unit 41) is comprised of a level detector 62 and a comparator 63. The lower limit level of the drain voltage is detected by the level detector 62 and the thus-detected level is compared at the comparator 63, with the reference voltage V_{ref} , and the resultant error signal is fed back to the gate of the FET T_1 via a clamp diode 64, so that the lower limit level of the signal S_{s1} is maintained at a constant level. The clamp diode 64 determines the aforesaid slice level, and a capacitor C_4 operates as a DC cut capacitor.

As explained above in detail, the slice amplifier using FET's can be put into practical use for high speed data transmission systems, such as a photo communication system, since the variances of the pinch-off voltage, the variance of the temperature, and the variance of the power source voltage are disregarded by the monitor and control units.

Claims

1. A slice amplifier characterized by the use of field effect transistors (FET's) operative to discriminate logics "0" and "1" of an input signal, and comprising:

control input of the current sink means 47, which increases (or decrease) the source voltage of the FET₁ to increase (or decrease) the lower limit level of the signal S_{s1} , to thereby maintain the lower limit level at the first constant level CL_1 . The above-mentioned operation also holds true for the second monitor and control unit 42, so as to maintain the lower limit level of the second sliced signal S_{s2} at the second constant level CL_2 . As apparent from the above description, the first and second monitor and control units 41 and 42, respectively, control the source voltages of the FET's T_1 and T_2 , while keeping their gate voltages at a fixed level, so that each gate-source voltage V_{GS} of the FET's T_1 and T_2 is controlled.

In Fig. 9, a zener diode ZD is inserted between the drain of the first FET T_1 and the gate of the second FET T_2 , which zener diode ZD acts as a DC level shifter. The diode ZD decreases the input level to be applied to the second FET T_2 by, for example about 5 V, to assure an optimum driving level for the second FET T_2 .

Further, in Fig. 9, resistors 49 and 50 are connected to the gates of the first and second FET's T_1 and T_2 . The resistor 49 (and the resistor 50) is a so-called gate resistor which is useful for preventing undesired oscillation of the first FET T_1 (and the second FET T_2). It is known that the input impedance of the FET often assumes a negative resistance, which may induce oscillation. The negative resistance is changed to a positive resistance by the addition of the resistor (49, 50).

In Fig. 9, the second slice level (SL_2) is preferably determined to be a level suitable as an input level of a logic circuit, as mentioned previously. If the output signal S_{out} is given to an emitter coupled logic (ECL) circuit, a diode D_1 is employed for the determination of the upper level of the output signal S_{out} (V_2). The diode D_1 operates as a DC level shifter with, for example, -0.8 V. Thus, the diode D_1 defines an upper limit level, i.e., -0.8 V, of a prescribed range (-0.8 V through -1.6 V). The ECL circuit is a high speed logic circuit for forming the D-flip flop FF shown in Fig. 1.

The waveforms of signals appearing at the portions A, B, and C have already been displayed with reference to Figs. 7A, 7B, and 7C.

Figure 10 is a circuit diagram illustrating an example of the lower limit level detector of Fig. 9. In Fig. 10, the detector 43 (and the detector 44) is connected between the FET T_1 (T_2) and the error amplifier 45 (46). A diode D_2 is connected with the drain of the FET T_1 (T_2) and made conductive every time the cathode level becomes lower than the anode level, so that a capacitor C_3 is charged to hold each lower limit level of the signal S_{s1} (S_{s2}). The charging voltage is applied to the error amplifier 45 (46).

Figure 11 is a circuit diagram illustrating an example of the current sink means of Fig. 9. In Fig. 11, the current sink means 47 (and the generator 48)

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Figure 12 is a detailed circuit diagram illustrating an example of an actual slice amplifier together with its peripheral circuit elements. In Fig. 12, members corresponding to those previously explained are indicated by the same reference numerals or characters. An equalizer 51 is mounted at a stage preceding the slice amplifier 31. The waveform reshaping part 12 (Fig. 1) is mounted at a following stage thereof. Reference numerals 52 and 53 represent usual ECL gates. The majority of the slice amplifier 31 of Fig. 12 is the same as previously explained, the only difference being that buffer amplifiers 43-3 and 44-3 are positively illustrated in this figure. It should be understood that the lower limit level detector 43 (and the detector 44) are classified into three parts, 43-1, 43-2, and 43-3 (and the parts 44-1, 44-2, and 44-3).

Figure 13 is a circuit diagram of a slice amplifier according to a second embodiment of the present invention. The difference between the aforesaid first embodiment and the second embodiment is that, in the second embodiment, the gate-source voltage V_{GS} of the FET is varied by controlling the gate voltage, not the source voltage as in the first embodiment. It should be understood that only an input side stage of the slice amplifier is illustrated for brevity. A monitor and control unit (corresponding to the first monitor and control unit 41) is comprised of a level detector 62 and a comparator 63. The lower limit level of the drain voltage is detected by the level detector 62 and the thus-detected level is compared at the comparator 63, with the reference voltage V_{ref} , and the resultant error signal is fed back to the gate of the FET T_1 via a clamp diode 64, so that the lower limit level of the signal S_{s1} is maintained at a constant level. The clamp diode 64 determines the aforesaid slice level, and a capacitor C_4 operates as a DC cut capacitor.

As explained above in detail, the slice amplifier using FET's can be put into practical use for high speed data transmission systems, such as a photo communication system, since the variances of the pinch-off voltage, the variance of the temperature, and the variance of the power source voltage are disregarded by the monitor and control units.

Claims

1. A slice amplifier characterized by the use of field effect transistors (FET's) operative to discriminate logics "0" and "1" of an input signal, and comprising :





first FET (T_1) for receiving, at a gate thereof, an input signal and outputting, at a drain thereof, a portion of said input signal which is above a predetermined first slice level ;

a first monitor and control unit (41) for receiving, from said first FET, a drain output as a first sliced signal (S_{s1}) and detecting lower limit level of said first sliced signal to control a gate-source voltage of said first FET (T_1) so that the thus-detected limit level is maintained at a predetermined first constant level ;

a second FET (T_2) for receiving, at a gate thereof, a drain output from said first FET and outputting, at a drain of said second FET, a portion of said first sliced signal which is above a predetermined second slice level and ;

a second monitor and control unit (41) for receiving, from said second FET (T_2), a drain output as a second sliced signal (S_{s2}) and detecting lower limit level of said second sliced signal to control a gate-source voltage of said second FET (T_2) so that the thus-detected limit level is maintained at a predetermined second constant level, thus said second sliced signal (S_{s2}) is produced as an output signal with respect to said input signal.

2. A slice amplifier using FET's as set forth in claim 1, wherein said first slice level is determined to be a pinch-off voltage of said first FET, and said second slice level is determined to be a pinch-off voltage of said second FET.

3. A slice amplifier using FET's as set forth in claim 2, wherein said first and second monitor and control units control each source voltage of said first and second FET's respectively, and further maintain said first and second sliced signals at said first and second constant levels, respectively, while keeping each gate voltage of said first and second FET's at a fixed level.

4. A slice amplifier using FET's as set forth in claim 3, wherein said first and second monitor and control units, respectively, comprise :

first and second detection means for detecting each lower limit level of said first and second sliced signals ;

first and second comparison means for comparing lower limit levels produced from said first and second detection means with first and second reference voltage levels to produce respective control signals ; and

first and second current sink means for supplying respective source voltages, in accordance with said respective control signals, said source voltages having levels such that said respective lower limit levels are equal to said first and second constant levels.

5. A slice amplifier using FET's as set forth in claim 3, wherein a zener diode for a DC level shift is

inserted between a drain of said first FET and a gate of said second FET.

6. A slice amplifier using FET's as set forth in claim 3, wherein each gate of said first and second FET's is provided with resistors for preventing undesirable oscillation of said first and second FET's.

7. A slice amplifier using FET's as set forth in claim 1, wherein said first slice level is determined to be a level for discriminating logics "0" and "1" of said input signal.

8. A slice amplifier using FET's as set forth in claim 1, wherein said second slice level is determined to be a level suitable as an input level of a logic circuit following said slice amplifier.

9. A slice amplifier using FET's as set forth in claim 1, wherein each of said monitor and control unit monitors a drain voltage of respective FET's and controls a gate voltage thereof, by way of a clamp diode, to control of a gate-source voltage of said FET.

Revendications

1. Amplificateur à découpage, caractérisé par la mise en oeuvre de transistors à effet de champ (FET) actifs pour discriminer les niveaux logiques "0" et "1" d'un signal d'entrée, et comprenant :

un premier transistor FET (T_1) pour recevoir, par sa grille, un signal d'entrée et pour sortir, par son drain, une partie dudit signal d'entrée qui est au-dessus d'un premier niveau de découpage prédéterminé ;

une première unité de contrôle et de réglage (41) pour recevoir, dudit premier transistor FET, un signal de sortie de drain comme premier signal découpé (S_{s1}) et pour détecter un niveau de limite inférieure dudit premier signal découpé afin de régler la tension de grille-source dudit premier transistor FET (T_1) de telle sorte que le niveau de limite ainsi détecté est maintenu à un premier niveau constant prédéterminé ;

un deuxième transistor FET (T_2) pour recevoir, par sa grille, un signal de sortie de drain dudit premier transistor FET et pour sortir, par le drain dudit deuxième transistor FET, une partie dudit premier signal découpé qui est au-dessus d'un deuxième niveau de découpage prédéterminé et ;
une deuxième unité de contrôle et de réglage (42) pour recevoir, dudit deuxième transistor FET (T_2), un signal de sortie de drain comme deuxième signal découpé (S_{s2}) et pour détecter le niveau de limite inférieure dudit deuxième signal découpé afin de régler la tension de grille-source dudit deuxième transistor FET (T_2) de telle sorte que le niveau de limite ainsi détecté est maintenu à un deuxième niveau constant prédéterminé, ledit deuxième signal découpé (S_{s2}) étant ainsi produit comme signal de sortie par rapport audit



signal d'entrée.

2. Amplificateur à découpage mettant en oeuvre des transistors FET selon la revendication 1, dans lequel

ledit premier niveau de découpage est déterminé comme étant une tension de pincement dudit premier transistor FET, et ledit deuxième niveau de découpage est déterminé comme étant une tension de pincement dudit deuxième transistor FET.

3. Amplificateur à découpage mettant en oeuvre des transistors FET selon la revendication 2, dans lequel lesdites première et deuxième unités de contrôle et de réglage règlent chaque tension de source desdits premier et deuxième transistors FET respectivement, et maintiennent en outre lesdits premier et deuxième signaux découpés respectivement auxdits premier et deuxième niveaux constants, tout en maintenant chaque tension de grille desdits premier et deuxième transistors FET à un niveau fixe.

4. Amplificateur à découpage mettant en oeuvre des transistors FET selon la revendication 3, dans lequel lesdites première et deuxième unités de contrôle et de réglage comprennent respectivement :

des premier et deuxième moyens détecteurs pour détecter chaque niveau de limite inférieure desdits premier et deuxième signaux découpés ;

des premier et deuxième moyens comparateurs pour comparer les niveaux de limite inférieure produits par lesdits premier et deuxième moyens détecteurs à des premier et deuxième niveaux de tension de référence afin de produire des signaux de commande respectifs ; et

des premier et deuxième moyens récepteurs de courant pour fournir des tensions de source respectives, selon lesdits signaux de commande respectifs, lesdites tensions de source ayant des niveaux tels que lesdits niveaux de limite inférieure respectifs sont égaux auxdits premier et deuxième niveaux constants.

5. Amplificateur à découpage mettant en oeuvre des transistors FET selon la revendication 3, dans lequel une diode de Zener servant à un décalage de niveau en courant continu est insérée entre le drain dudit premier transistor FET et la grille dudit deuxième transistor FET.

6. Amplificateur à découpage mettant en oeuvre des transistors FET selon la revendication 3, dans lequel chaque grille desdits premier et deuxième transistors FET est pourvue de résistances pour empêcher une oscillation indésirable desdits premier et deuxième transistors FET.

7. Amplificateur à découpage mettant en oeuvre des transistors FET selon la revendication 1, dans lequel ledit premier niveau de découpage est déterminé comme étant un niveau pour discriminer les niveaux logiques "0" et "1" dudit signal d'entrée.

8. Amplificateur à découpage mettant en oeuvre des transistors FET selon la revendication 1, dans

lequel ledit deuxième niveau de découpage est déterminé comme étant un niveau convenant comme niveau d'entrée d'un circuit logique à la suite dudit amplificateur à découpage.

9. Amplificateur à découpage mettant en oeuvre des transistors FET selon la revendication 1, dans lequel chacune desdites unités de contrôle et de réglage contrôle la tension de drain des transistors FET respectifs et règle la tension de grille de ceux-ci, au moyen d'une diode de blocage, pour régler la tension de grille-source desdits transistors FET.

Ansprüche

1. Begrenzungsverstärker, gekennzeichnet durch die Verwendung von Feldeffekttransistoren (FET's), welche betrieben werden, um logische Zustände "0" und "1" eines Eingangssignals zu unterscheiden, und umfassen :

einen ersten Feldeffekttransistor (T_1) zum Empfangen eines Eingangssignales an seinem Gate, und zum Ausgeben eines Teiles des Eingangssignales, welcher oberhalb einem vorbestimmten ersten Begrenzungspegel ist, an seinem Drain ; eine erste Überwachungs- und Steuerungseinheit (41) zum Empfangen eines Drain-Ausgangssignals als ein erstes begrenztes Signal (S_{11}) von dem ersten Feldeffekttransistor und zum Ermitteln eines unteren Begrenzungspegels des ersten begrenzten Signals, um eine Gate-Source-Spannung des ersten Feldeffekttransistors (T_1) zu steuern, so daß der so ermittelte Begrenzungspegel auf einem vorbestimmten ersten konstanten pegel gehalten wird ;

einen zweiten Feldeffekttransistor (T_2) zum Empfangen eines Drain-Ausgangssignales an seinem Gate von dem ersten Feldeffekttransistor, und zum Ausgeben eines Teiles des ersten Begrenzungssignals, welcher oberhalb eines vorbestimmten zweiten Begrenzungspegels ist, an seinem Drain ; und

eine zweite Überwachungs- und Steuerungseinheit (41) zum Empfangen eines Drain-Ausgangssignales als ein zweites Begrenztes Signal (S_{22}) vom zweiten Feldeffekttransistor (T_2) und zum Ermitteln eines unteren Begrenzungspegels des zweiten begrenzten Signales, um eine Gate-Source-Spannung des zweiten Feldeffekttransistors (T_2) zu steuern, so daß der so ermittelte Begrenzungspegel auf einem vorbestimmten zweiten konstanten Pegel gehalten wird, wobei somit das zweite begrenzte Signal (S_{22}) als ein Ausgangssignal mit Bezug auf das Eingangssignal erzeugt wird.

2. Begrenzungsverstärker, welcher Feldeffekttransistoren verwendet, nach Anspruch 1, dadurch gekennzeichnet, daß der erste Begrenzungspegel



bestimmt ist, eine Abschnürspannung des ersten Feldeffekttransistors zu sein, und der zweite Begrenzungspegel bestimmt ist, eine Abschnürspannung des zweiten Feldeffekttransistors zu sein.

3. Begrenzungsverstärker, welcher Feldeffekttransistoren verwendet, nach Anspruch 2, dadurch gekennzeichnet, daß die ersten und zweiten Überwachungs- und Steuerungseinheiten jede Source-Spannung der ersten bzw. zweiten Feldeffekttransistoren steuern, und ferner die ersten bzw. zweiten begrenzten Signale auf den ersten bzw. zweiten konstanten Pegeln halten, während sie jede Gatespannung der ersten und zweiten Feldeffekttransistoren auf einem festen Pegel halten.

4. Begrenzungsverstärker, welcher Feldeffekttransistoren verwendet, nach Anspruch 3, dadurch gekennzeichnet, daß die ersten bzw. zweiten Überwachungs- und Steuerungseinheiten umfassen :

erste und zweite Detektiereinrichtungen zum Ermitteln jedes unteren Begrenzungspegels der ersten und zweiten Begrenzungssignale ;

erste und zweite Vergleichseinrichtungen zum Vergleichen von von der ersten und zweiten Detektiereinrichtung erzeugten unteren Begrenzungspegeln mit ersten und zweiten Bezugsspannungspegeln, um jeweilige Steuerungssignale zu erzeugen ; und

erste und zweite Stromsenken-Einrichtungen zum Tiefern von jeweiligen Source-Spannungen in Übereinstimmung mit den jeweiligen Steuerungssignalen, wobei die Source-Spannungen Pegel aufweisen, so daß die jeweiligen unteren Grenzpegel gleich den ersten bzw. zweiten konstanten Pegeln sind.

5. Begrenzungsverstärker, welcher Feldeffekttransistoren verwendet, nach Anspruch 3, dadurch gekennzeichnet, daß eine Zenerdiode für eine Gleichspannungs-pegelverschiebung zwischen einem Drain des ersten Feldeffekttransistors und einem Gate des zweiten Feldeffekttransistors eingefügt ist.

6. Begrenzungsverstärker, welcher Feldeffekttransistoren verwendet, nach Anspruch 3, dadurch gekennzeichnet, daß jedes Gate der ersten und zweiten Feldeffekttransistoren mit Widerständen versehen ist, um eine unerwünschte Oszillation der ersten und zweiten Feldeffekttransistoren zu verhindern.

7. Begrenzungsverstärker, welcher Feldeffekttransistoren verwendet, nach Anspruch 1, dadurch gekennzeichnet, daß der erste Begrenzungspegel bestimmt ist, ein Pegel zum Unterscheiden von logischen Zuständen "0" und "1" des Eingangssignals zu sein.

8. Begrenzungsverstärker, welcher Feldeffekttransistoren verwendet, nach Anspruch 1, dadurch gekennzeichnet, daß der zweite Begrenzungspegel bestimmt ist, ein pegel zu sein, der geeignet ist als ein Eingangspegel eines Logikschaltkreises, welcher auf

den Begrenzungsverstärker folgt.

9. Begrenzungsverstärker, welcher Feldeffekttransistoren verwendet, nach Anspruch 1, dadurch gekennzeichnet, daß jede der Überwachungs- und Steuerungseinheiten eine Drain-Spannung jeweiliger Feldeffekttransistoren überwacht, und eine Gatespannung davon mittels einer Klemmdiode steuert, um eine Gate-Source-Spannung des Feldeffekttransistors zu steuern.